

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN - PCS/cellular radio and WLL applications.

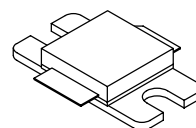
- Typical 2-carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 450$ mA, $P_{out} = 11.5$ Watts Avg., $f = 2157$ MHz, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
Power Gain — 16 dB
Drain Efficiency — 27.7%
IM3 @ 10 MHz Offset — -37 dBc in 3.84 MHz Channel Bandwidth
ACPR @ 5 MHz Offset — -40 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2140 MHz, 50 Watts CW Output Power

Features

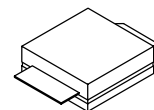
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 32 mm, 13 inch Reel.

MRF6S21050LR3
MRF6S21050LSR3

2110-2170 MHz, 11.5 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465E-04, STYLE 1
NI-400
MRF6S21050LR3



CASE 465F-04, STYLE 1
NI-400S
MRF6S21050LSR3

Table 1. Maximum Ratings

| Rating | Symbol | Value | Unit |
|--------------------------------------|-----------|--------------|------|
| Drain-Source Voltage | V_{DSS} | -0.5, +68 | Vdc |
| Gate-Source Voltage | V_{GS} | -0.5, +12 | Vdc |
| Storage Temperature Range | T_{stg} | - 65 to +150 | °C |
| Case Operating Temperature | T_C | 150 | °C |
| Operating Junction Temperature (1,2) | T_J | 225 | °C |

Table 2. Thermal Characteristics

| Characteristic | Symbol | Value (2,3) | Unit |
|--|-----------------|--------------|------|
| Thermal Resistance, Junction to Case Case Temperature 80°C, 50 W CW Case Temperature 76°C, 12 W CW | $R_{\theta JC}$ | 1.16 1.28 | °C/W |

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

| Test Methodology | Class |
|---------------------------------------|---------------|
| Human Body Model (per JESD22-A114) | 1C (Minimum) |
| Machine Model (per EIA/JESD22-A115) | A (Minimum) |
| Charge Device Model (per JESD22-C101) | III (Minimum) |

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

Off Characteristics

| | | | | | |
|---|-----------|---|---|----|-----------------|
| Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) | I_{DSS} | — | — | 10 | μAdc |
| Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) | I_{DSS} | — | — | 1 | μAdc |
| Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$) | I_{GSS} | — | — | 1 | μAdc |

On Characteristics

| | | | | | |
|---|--------------|---|------|-----|-----|
| Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\ \mu\text{Adc}$) | $V_{GS(th)}$ | 1 | 2 | 3 | Vdc |
| Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 450\text{ mAdc}$, Measured in Functional Test) | $V_{GS(Q)}$ | 2 | 2.9 | 4 | Vdc |
| Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.1\text{ Adc}$) | $V_{DS(on)}$ | — | 0.21 | 0.3 | Vdc |

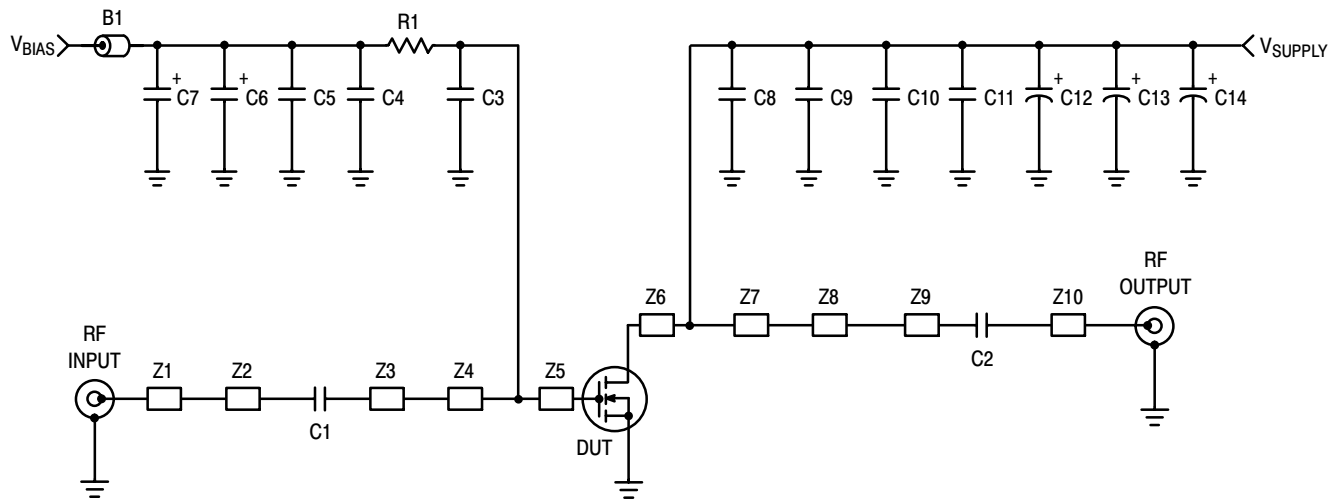
Dynamic Characteristics ⁽¹⁾

| | | | | | |
|---|-----------|---|------|---|----|
| Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$) | C_{rss} | — | 0.75 | — | pF |
|---|-----------|---|------|---|----|

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 450\text{ mA}$, $P_{out} = 11.5\text{ W Avg.}$, $f = 2157\text{ MHz}$, 2-carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset. IM3 measured in 3.84 MHz Bandwidth @ $\pm 10\text{ MHz}$ Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

| | | | | | |
|------------------------------|----------|----|------|-----|-----|
| Power Gain | G_{ps} | 15 | 16 | 18 | dB |
| Drain Efficiency | η_D | 26 | 27.7 | — | % |
| Intermodulation Distortion | IM3 | — | -37 | -35 | dBc |
| Adjacent Channel Power Ratio | ACPR | — | -40 | -38 | dBc |
| Input Return Loss | IRL | — | -15 | -9 | dB |

1. Part is internally matched both on input and output.

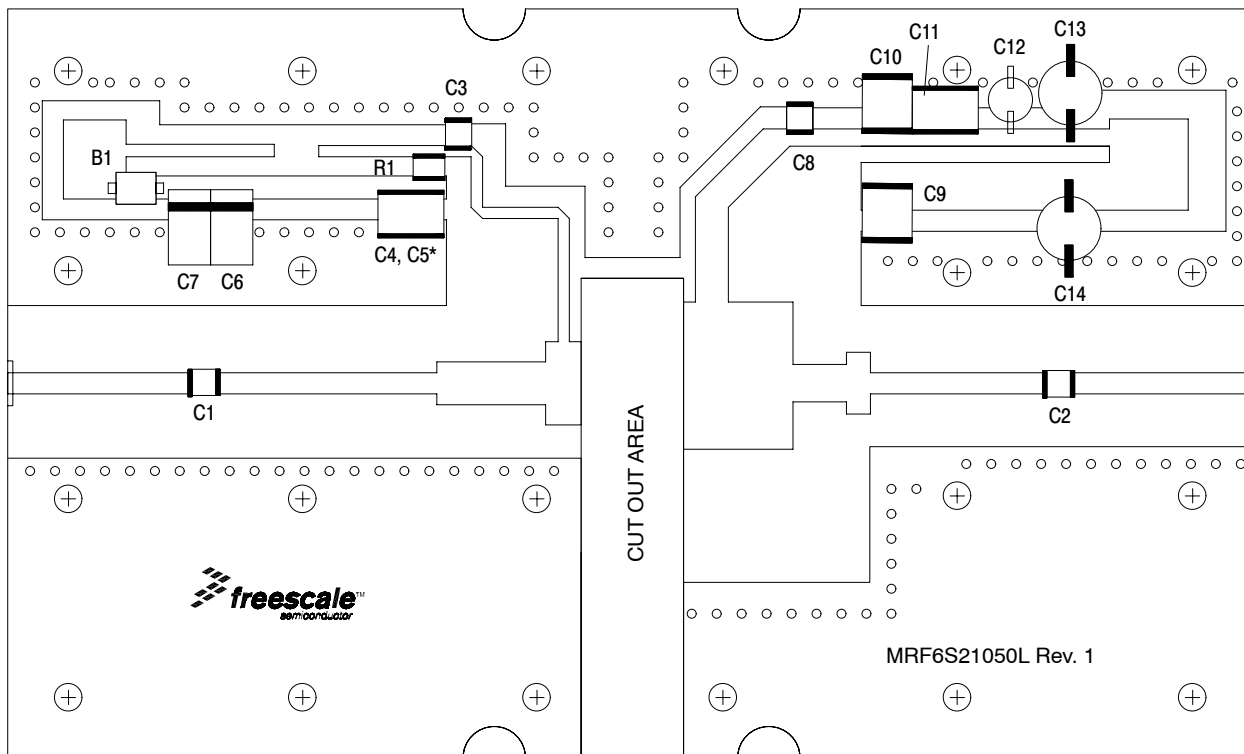


| | | | |
|---------|----------------------------|-----|--|
| Z1, Z10 | 0.750" x 0.084" Microstrip | Z6 | 0.113" x 0.590" Microstrip |
| Z2 | 0.905" x 0.084" Microstrip | Z7 | 0.325" x 0.590" Microstrip |
| Z3 | 0.435" x 0.173" Microstrip | Z8 | 0.214" x 0.150" Microstrip |
| Z4 | 0.073" x 0.333" Microstrip | Z9 | 0.723" x 0.084" Microstrip |
| Z5 | 0.070" x 0.333" Microstrip | PCB | Arlon CuClad 250GX-0300-55-22, 0.030", $\epsilon_r = 2.55$ |

Figure 1. MRF6S21050LR3 (LSR3) Test Circuit Schematic

Table 5. MRF6S21050LR3 (LSR3) Test Circuit Component Designations and Values

| Part | Description | Part Number | Manufacturer |
|----------------|---|--------------------|--------------|
| B1 | Bead, Surface Mount | 2743019447 | Fair-Rite |
| C1, C2, C3, C8 | 6.8 pF Chip Capacitors | ATC100B6R8CT500XT | ATC |
| C4 | 0.01 μ F Chip Capacitor | C1825C103J1RAC | Kemet |
| C5, C11 | 2.2 μ F, 50 V Chip Capacitors | C1825C225J5RAC | Kemet |
| C6 | 22 μ F, 25 V Tantalum Capacitor | T491D226K025AT | Kemet |
| C7 | 47 μ F, 16 V Tantalum Capacitor | T491D476K016AT | Kemet |
| C9, C10 | 10 μ F, 50 V Chip Capacitors | GRM55DR61H106KA88B | Murata |
| C12 | 47 μ F, 50 V Electrolytic Capacitor | EMVY500ADA470MF80G | Nippon |
| C13, C14 | 220 μ F, 50 V Electrolytic Capacitors | EMVY500ADA221MJA0G | Chemi-Con |
| R1 | 3.3 Ω , 1/3 W Chip Resistor | CRCW12103R30FKEA | Vishay |



* C4 on bottom, C5 on top.

Figure 2. MRF6S21050LR3(LSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

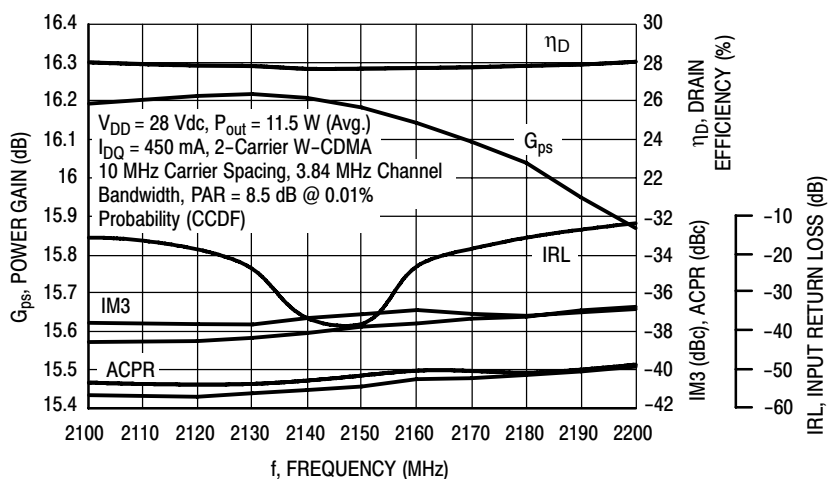


Figure 3. 2-Carrier W-CDMA Broadband Performance @ $P_{out} = 11.5$ Watts

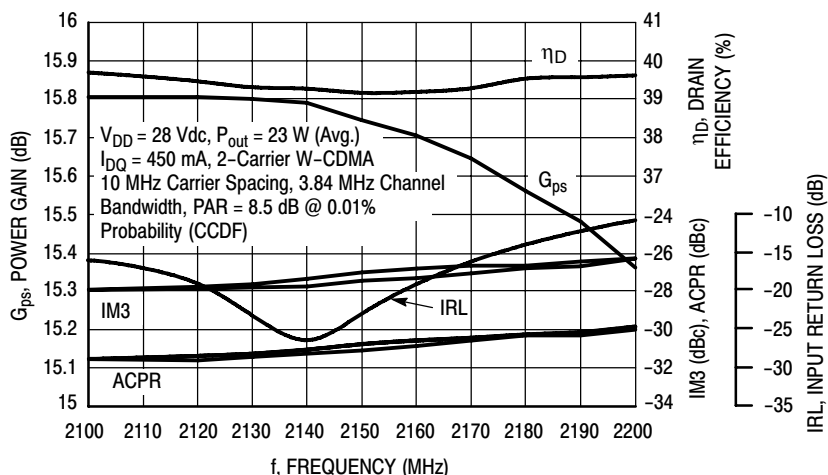


Figure 4. 2-Carrier W-CDMA Broadband Performance @ $P_{out} = 23$ Watts

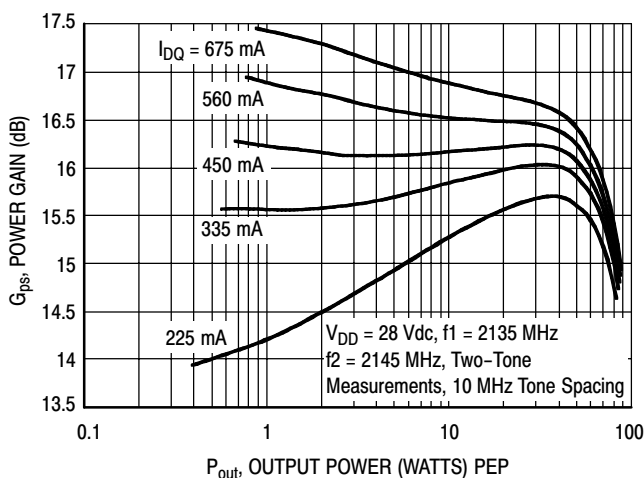


Figure 5. Two-Tone Power Gain versus Output Power

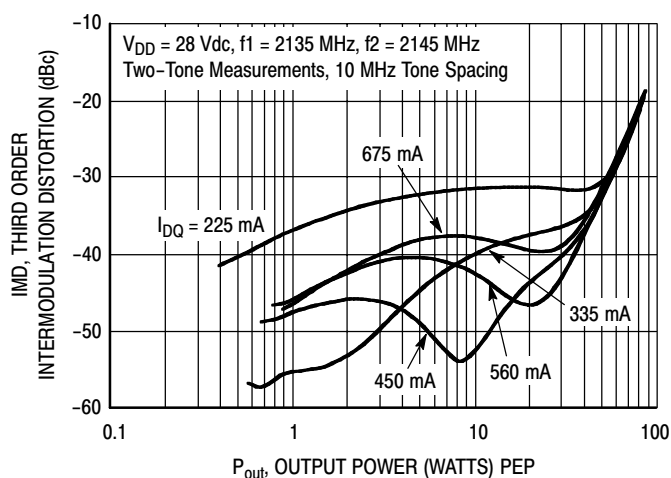


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

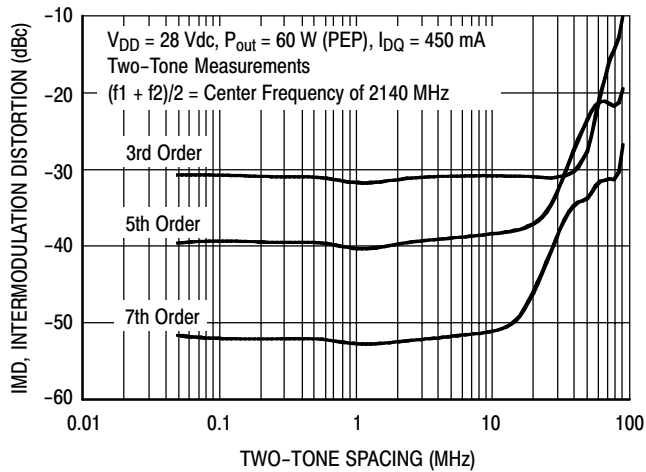


Figure 7. Intermodulation Distortion Products versus Tone Spacing

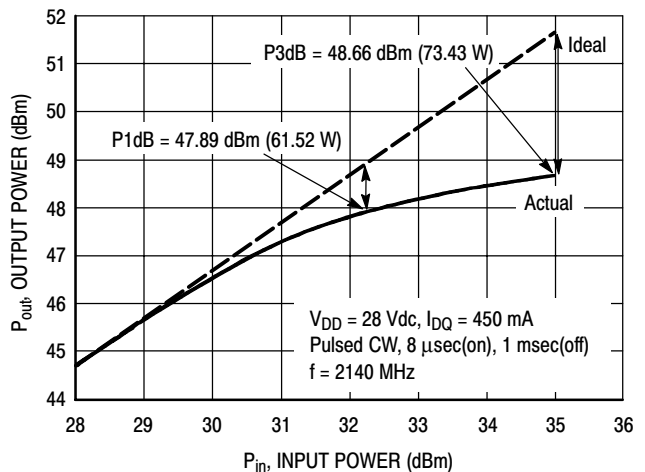


Figure 8. Pulsed CW Output Power versus Input Power

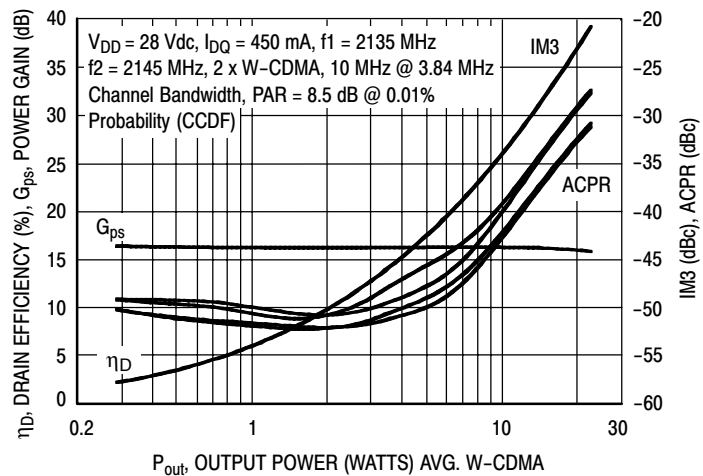


Figure 9. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

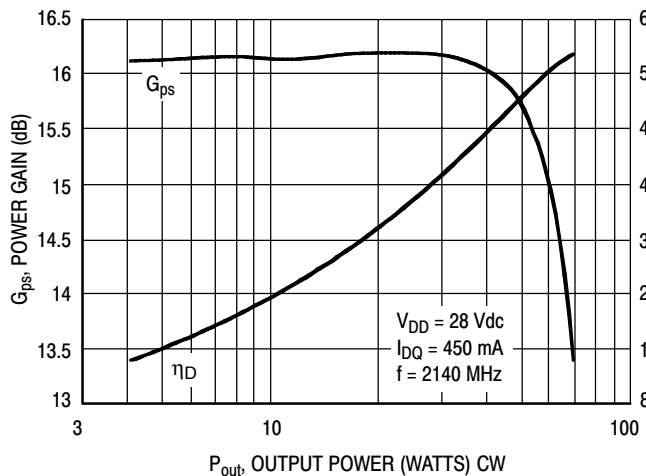


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

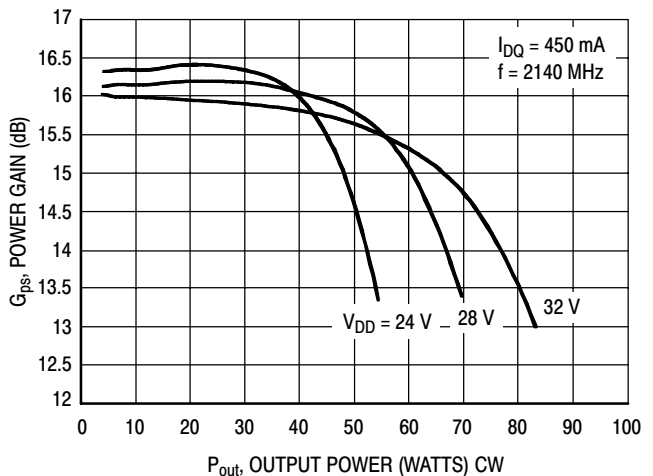
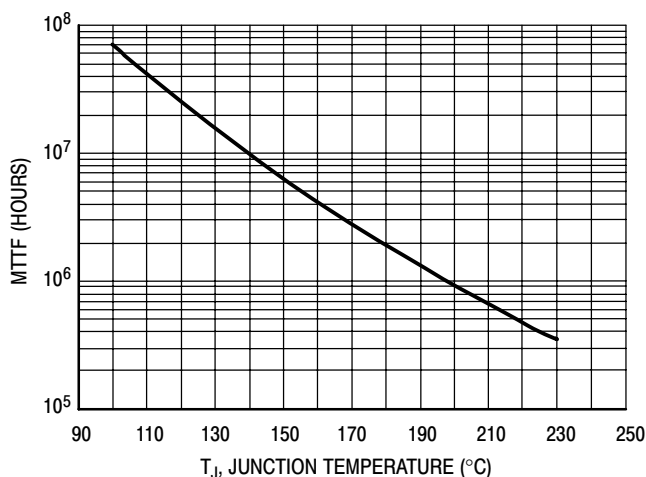


Figure 11. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28$ Vdc, $P_{out} = 11.5$ W Avg., and $\eta_D = 27.7\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 12. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

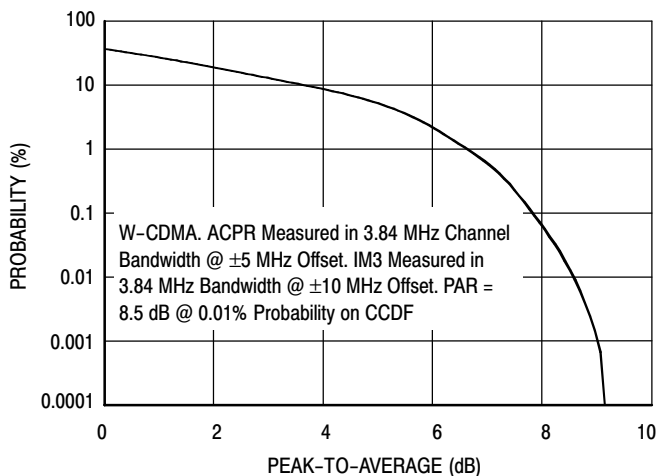


Figure 13. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

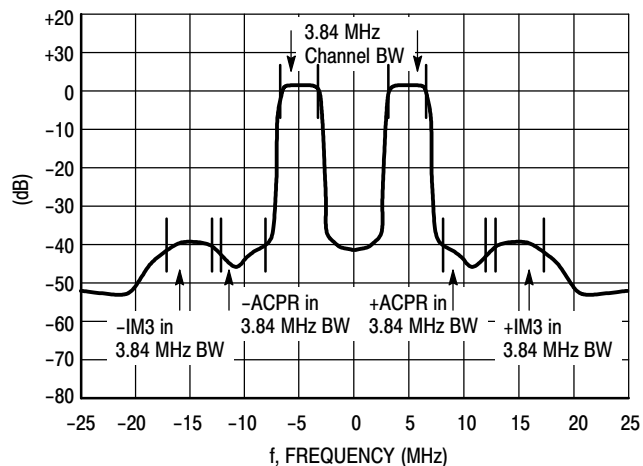
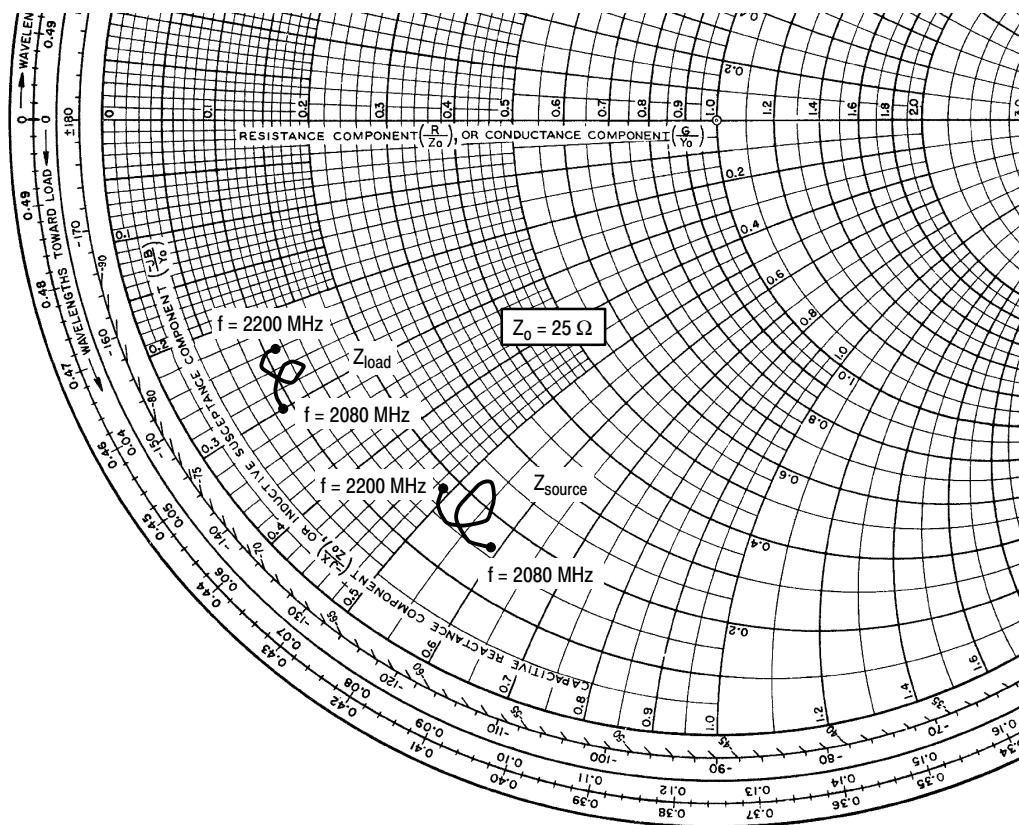


Figure 14. 2-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 450 \text{ mA}$, $P_{out} = 11.5 \text{ W Avg.}$

| f MHz | Z_{source} Ω | Z_{load} Ω |
|----------|--------------------------|------------------------|
| 2080 | 4.09 - j14.65 | 2.36 - j7.52 |
| 2090 | 3.74 - j13.95 | 2.25 - j7.11 |
| 2100 | 3.95 - j13.36 | 2.40 - j6.78 |
| 2110 | 4.44 - j13.00 | 2.68 - j6.59 |
| 2120 | 5.03 - j12.89 | 2.99 - j6.52 |
| 2130 | 5.55 - j13.05 | 3.26 - j6.64 |
| 2140 | 5.76 - j13.26 | 3.32 - j6.68 |
| 2150 | 5.57 - j13.70 | 3.20 - j6.87 |
| 2160 | 4.86 - j13.92 | 2.82 - j6.93 |
| 2170 | 4.04 - j13.61 | 2.44 - j6.70 |
| 2180 | 3.69 - j12.91 | 2.33 - j6.29 |
| 2190 | 3.91 - j12.44 | 2.49 - j6.05 |
| 2200 | 4.41 - j12.32 | 2.77 - j5.96 |

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

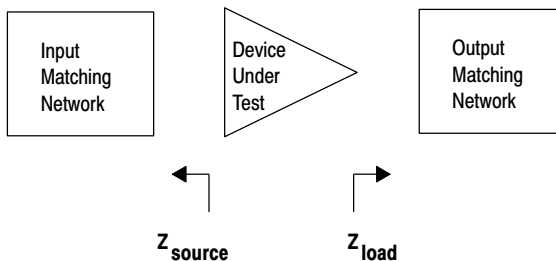
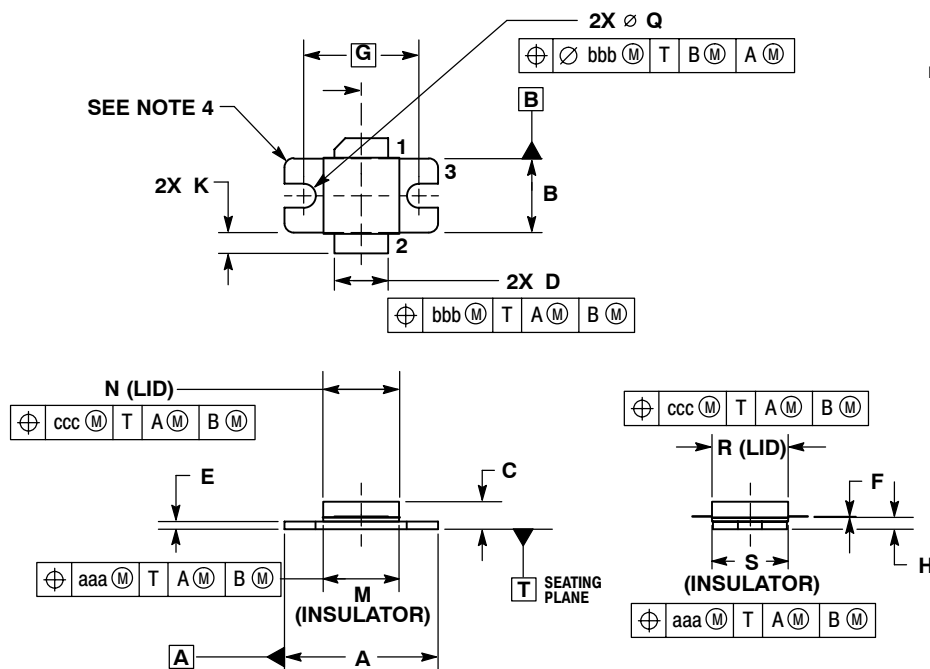


Figure 15. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS

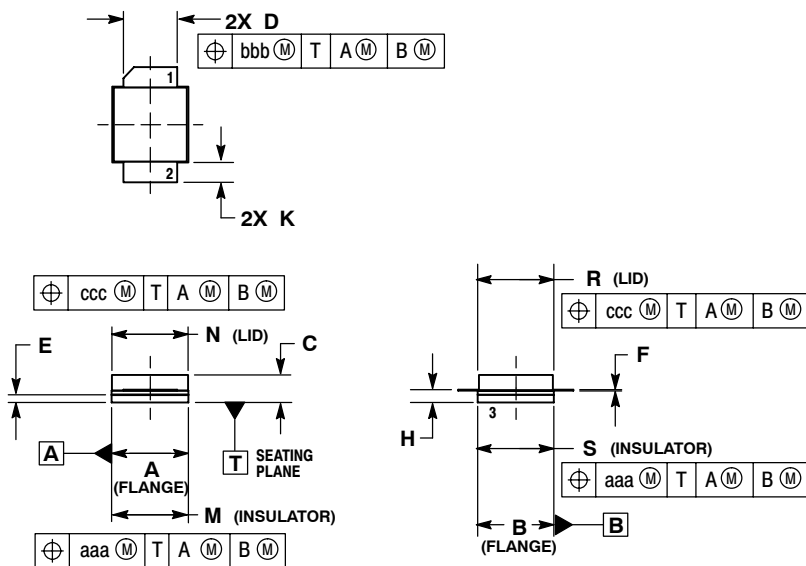


- NOTES:
1. CONTROLLING DIMENSION: INCH.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. INFORMATION ONLY: CORNER BREAK (4X) TO BE .060±.005 (1.52±0.13) RADIUS OR .06±.005 (1.52±0.13) x 45° CHAMFER.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------------------|--------------------|--------------------|-------------------|
| | MIN | MAX | MIN | MAX |
| A | .795 | .805 | 20.19 | 20.44 |
| B | .380 | .390 | 9.65 | 9.9 |
| C | .125 | .163 | 3.17 | 4.14 |
| D | .275 | .285 | 6.98 | 7.24 |
| E | .035 | .045 | 0.89 | 1.14 |
| F | .004 | .006 | 0.10 | 0.15 |
| G | .600 BSC | | 15.24 BSC | |
| H | .057 | .067 | 1.45 | 1.7 |
| K | .092 | .122 | 2.33 | 3.1 |
| M | .395 | .405 | 10 | 10.3 |
| N | .395 | .405 | 10 | 10.3 |
| Q | \varnothing .120 | \varnothing .130 | \varnothing 3.05 | \varnothing 3.3 |
| R | .395 | .405 | 10 | 10.3 |
| S | .395 | .405 | 10 | 10.3 |
| aaa | .005 BSC | | 0.127 BSC | |
| bbb | .010 BSC | | 0.254 BSC | |
| ccc | .015 BSC | | 0.381 BSC | |

STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

**CASE 465E-04
 ISSUE F
 NI-400
 MRF6S21050LR3**



- NOTES:
1. CONTROLLING DIMENSION: INCH.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

| DIM | INCHES | | MILLIMETERS | |
|-----|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .395 | .405 | 10.03 | 10.29 |
| B | .395 | .405 | 10.03 | 10.29 |
| C | .125 | .163 | 3.18 | 4.14 |
| D | .275 | .285 | 6.98 | 7.24 |
| E | .035 | .045 | 0.89 | 1.14 |
| F | .004 | .006 | 0.10 | 0.15 |
| H | .057 | .067 | 1.45 | 1.70 |
| K | .092 | .122 | 2.34 | 3.10 |
| M | .395 | .405 | 10.03 | 10.29 |
| N | .395 | .405 | 10.03 | 10.29 |
| R | .395 | .405 | 10.03 | 10.29 |
| S | .395 | .405 | 10.03 | 10.29 |
| aaa | .005 REF | | 0.127 REF | |
| bbb | .010 REF | | 0.254 REF | |
| ccc | .015 REF | | 0.38 REF | |

STYLE 1:
 PIN 1. DRAIN
 2. GATE
 3. SOURCE

**CASE 465F-04
 ISSUE E
 NI-400S
 MRF6S21050LSR3**

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

| Revision | Date | Description |
|----------|-----------|--|
| 2 | Dec. 2008 | <ul style="list-style-type: none"> • Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN13232, p. 1, 2 • Removed Low Gold Plating bullet from Features section as functionality is standard, p. 1 • Removed Total Device Dissipation from Max Ratings table as data was redundant (information already provided in Thermal Characteristics table), p. 1 • Operating Junction Temperature increased from 200°C to 225°C in Maximum Ratings table and related “Continuous use at maximum temperature will affect MTTF” footnote added, p. 1 • Corrected V_{DS} to V_{DD} in the RF test condition voltage callout for $V_{GS(Q)}$, and added “Measured in Functional Test”, On Characteristics table, p. 2 • Removed Forward Transconductance from On Characteristics table as it no longer provided usable information, p. 2 • Updated PCB information to show more specific material details, Fig. 1, Test Circuit Schematic, p. 3 • Updated Part Numbers in Table 5, Component Designations and Values, to latest RoHS compliant part numbers, p. 3 • Removed lower voltage tests from Fig. 11, Power Gain versus Output Power, due to fixed tuned fixture limitations, p. 6 • Replaced Fig. 12, MTTF versus Junction Temperature, with updated graph. Removed Amps² and listed operating characteristics and location of MTTF calculator for device, p. 7 • Added Product Documentation and Revision History, p. 10 |

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